# PSMN1R0-30YLD

#### N-channel 30 V, 1.0 mΩ, 300 A logic level MOSFET in LFPAK56 using NextPowerS3 Technology

Symbol	Parameter	Conditions		Min	Tun	Max	Unit
Symbol	Farameter	Conditions		IVIIII	Тур	Wax	Unit
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 2</u>	[1]	-	-	300	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	238	W
Tj	junction temperature			-55	-	175	°C
Static charac	teristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 10		-	1	1.3	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 10		-	0.79	1.02	mΩ
Dynamic cha	racteristics						,
Q <sub>GD</sub>	gate-drain charge	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; Fig. 12; Fig. 13		-	10.9	16.35	nC
Q <sub>G(tot)</sub>	total gate charge	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; Fig. 12; Fig. 13		-	38.2	57.3	nC
Source-drain	diode						
S	softness factor	$I_{S} = 25 \text{ A}; V_{GS} = 0 \text{ V}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s};$ $V_{DS} = 15 \text{ V}; \underline{\text{Fig. 16}}$		-	0.95	-	

[1] 300A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, Thermal design and operating temperature.

### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G C C
4	G	gate	ប្រុប្បូប្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

# 6. Ordering information

Table 3. Ordering inf	formation				
Type number	Package				
	Name	Description	Version		
PSMN1R0-30YLD	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

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#### Marking 7.

Table 4. Marking codes	
Type number	Marking code
PSMN1R0-30YLD	1D030L

#### Limiting values 8.

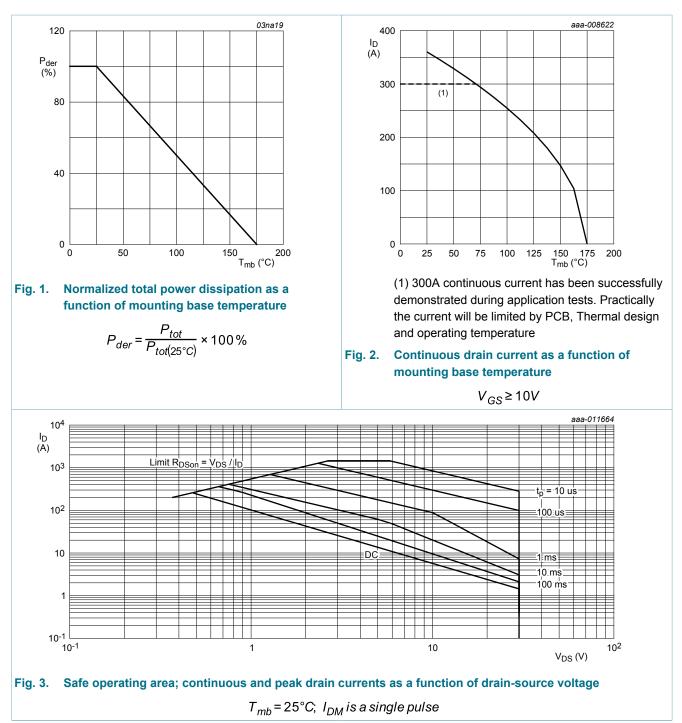
Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	30	V
V <sub>DGR</sub>	drain-gate voltage	25 °C $\leq$ T <sub>j</sub> $\leq$ 175 °C; R <sub>GS</sub> = 20 kΩ		-	30	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	238	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	300	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>		-	255	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$ ; Fig. 3		-	1441	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ		1500	-	V
Source-dra	in diode	1	1			
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	198	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	1441	А
Avalanche	ruggedness	1				
I <sub>AS</sub>	non-repetitive avalanche current	$\label{eq:V_sup} \begin{split} V_{sup} &\leq 30 \text{ V};  V_{GS} = 10 \text{ V};  T_{j(\text{init})} = 25 ^{\circ}\text{C}; \\        $	[2]	-	190	A
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 25 A; $V_{sup} \le 30$ V; $R_{GS}$ = 50 Ω; unclamped; $t_p$ = 3.3 ms	[2]	-	1588	mJ

[1] 300A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, Thermal design and operating temperature.

Protected by 100% test [2]

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### 9. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 4	-	0.56	0.63	K/W
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#### N-channel 30 V, 1.0 mΩ, 300 A logic level MOSFET in LFPAK56 using NextPowerS3 Technology

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	Fig. 5	-	50	-	K/W
	from junction to ambient	<u>Fig. 6</u>	-	125	-	K/W

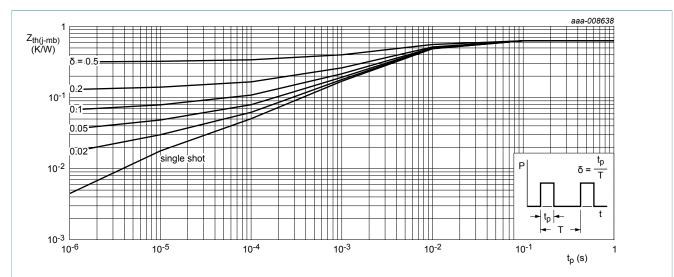
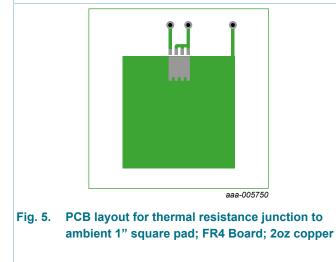


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration



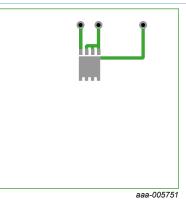


Fig. 6. PCB layout for thermal resistance junction to ambient minimum footprint; FR4 Board; 2oz copper

### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · ·	l.			
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	30	-	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	27	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 2 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.2	1.75	2.2	V

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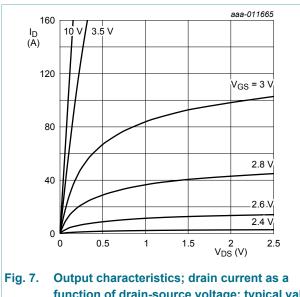
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ΔV <sub>GS(th)</sub> /ΔT	gate-source threshold voltage variation with temperature	25 °C ≤ T <sub>j</sub> ≤ 150 °C	-	-4.9	-	mV/K
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 24 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>DS</sub> = 24 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	2.8	-	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1	1.3	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 150 °C; Fig. 11; Fig. 10	-	-	2.15	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 10	-	0.79	1.02	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 150 °C; Fig. 11; Fig. 10	-	-	1.7	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	1.22	2.44	Ω
Dynamic cha	aracteristics					J
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 10 V; Fig. 12; Fig. 13	-	80.9	121.35	nC
		I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 4.5 V; Fig. 12; Fig. 13	-	38.2	57.3	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	72	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D$ = 25 A; $V_{DS}$ = 15 V; $V_{GS}$ = 4.5 V;	-	12.5	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	Fig. 12; Fig. 13	-	7.8	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge		-	4.7	-	nC
Q <sub>GD</sub>	gate-drain charge		-	10.9	16.35	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; <u>Fig. 12</u> ; <u>Fig. 13</u>	-	2.6	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	5732	8598	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 14</u>	-	2424	3636	pF
C <sub>rss</sub>	reverse transfer capacitance		-	340	510	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 15 V; R <sub>L</sub> = 1 Ω; V <sub>GS</sub> = 4.5 V;	-	32.4	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	44.4	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	43	-	ns
t <sub>f</sub>	fall time		-	31.7	-	ns

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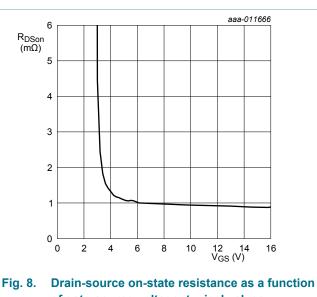
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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Q <sub>oss</sub>	output charge	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 15 V; f = 1 MHz; T <sub>j</sub> = 25 °C		-	55.9	-	nC
Source-dra	in diode			•			
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 25 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 15</u>		-	0.77	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{\rm S}$ = 25 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V;		-	51.8	103.6	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 15 V; <u>Fig. 16</u>	[1]	-	67.1	134.2	nC
t <sub>a</sub>	reverse recovery rise time			-	26.5	-	ns
t <sub>b</sub>	reverse recovery fall time			-	25.3	-	ns
S	softness factor	-		-	0.95	-	



[1] includes capacitive recovery



function of drain-source voltage; typical values  $T_i = 25^{\circ}C$ 

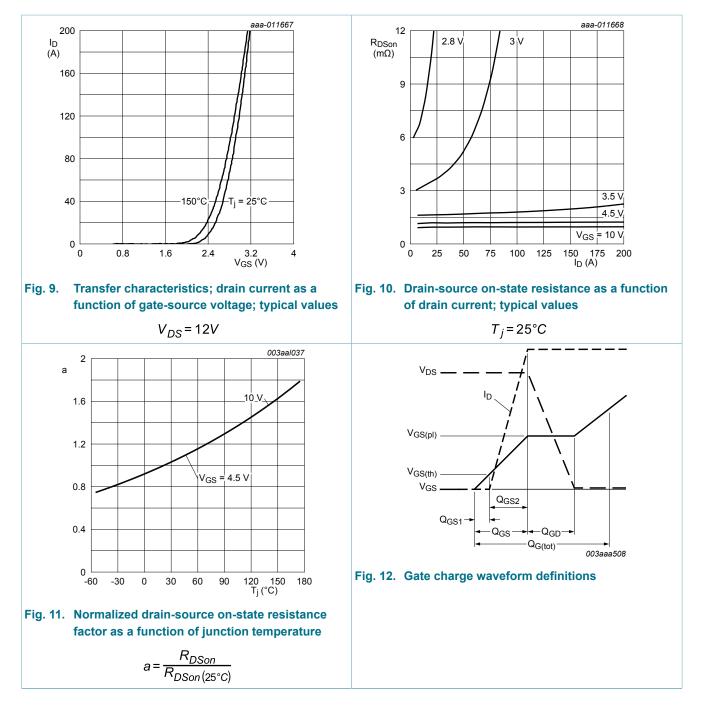


 $T_j = 25^{\circ}C; I_D = 25A$ 

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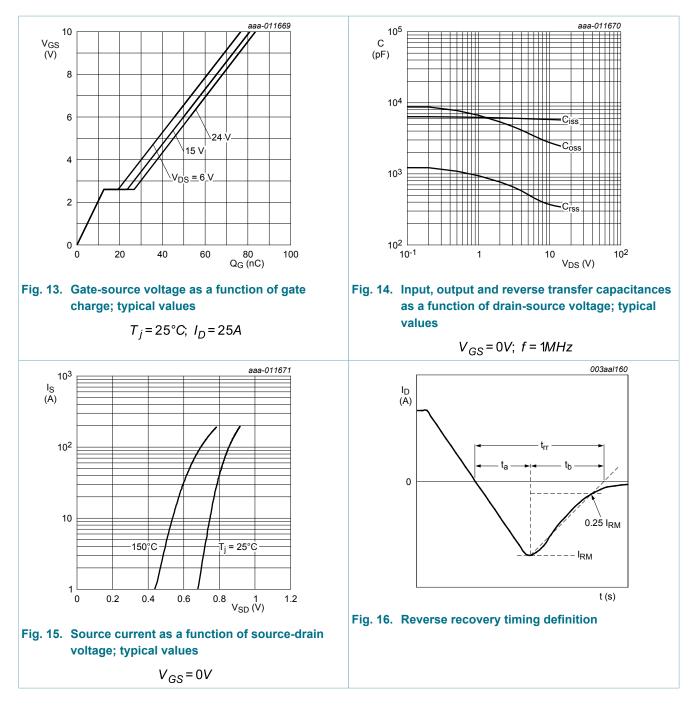
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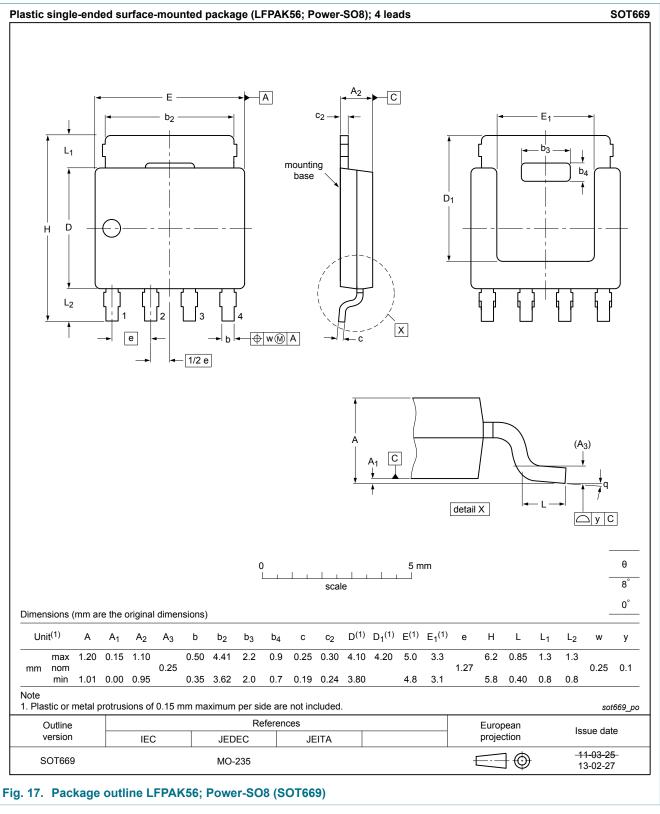
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#### N-channel 30 V, 1.0 mΩ, 300 A logic level MOSFET in LFPAK56 using NextPowerS3 Technology

### 11. Package outline



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Product data sheet

#### N-channel 30 V, 1.0 mΩ, 300 A logic level MOSFET in LFPAK56 using NextPowerS3 Technology

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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